

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Ryoji HOSHI et al.

Application No.: New U.S. National Stage of PCT/JP03/08671

Filed: January 4, 2005

DT12 Rec'd PCT/PTO 04 JAN 2005

Docket No.: 122336

For: A SILICON WAFER FOR EPITAXIAL GROWTH, AN EPITAXIAL WAFER, AND A
METHOD FOR PRODUCING ITINFORMATION DISCLOSURE STATEMENT

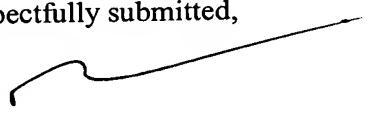
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Pursuant to 37 CFR §1.56, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached PTO-1449. Unless otherwise indicated herein, one copy of each reference is attached. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

- 1. This Information Disclosure Statement is being filed (a) within three months of the U.S. filing date of this non-CPA application, OR (b) before the mailing date of a first Office Action on the merits in the present application. No certification or fee is required.
- 2. Relevance of references 2-4 is discussed in the present specification.
- 3. References 1, 5-6, 8-9 were cited in the International Search Report. An English language version of the International Search Report is attached for the Examiner's information.
- 4. In accordance with 37 CFR §1.98(a)(2)(i), copies of any U.S. patents and patent application publications are not attached.
- 5. English language Abstracts of non-English language references 2-9 are attached hereto.
- 6. Computer-generated English language translation of the following Japanese references have been obtained from the website of the Japanese Patent Office ([<http://www.jpo.go.jp>]), and are attached, but have not been reviewed for accuracy. See References 2-4, 6-9.
- 7. Reference 7 corresponds to Reference 1. Reference 3 corresponds to WO 01/38611 A1, which is cited in the International Search Report.

Respectfully submitted,


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Form PTO-1449 (REV. 8-83)			US Dept. of Commerce PATENT & TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)		ATTY DOCKET NO. 122336		APPLICATION NO. New U.S. National Stage of PCT/JP03/08671	
					APPLICANTS Ryoji HOSHI et al.			
					FILING DATE January 4, 2005			
U.S. PATENT DOCUMENTS								
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME		CLASS	SUB CLASS	
	1.	US 2002/0000189 A1	01/03/2002	Tadami TANAKA et al.				
FOREIGN PATENT DOCUMENTS								
		DOCUMENT NUMBER	DATE	COUNTRY		CLASS	SUB CLASS	
	2.	JP-A-2000-044389 w/ abst. & trans.	02/15/2000	JAPAN				
	3.	JP-A-2001-151596 w/ abst. & trans.	06/05/2001	JAPAN				
	4.	JP-A-2000-219598 w/ abst. & trans.	08/08/2000	JAPAN				
	5.	WO 01/27362 A1 w/ abst.	04/19/2001	JAPAN				
	6.	JP-A-2001-274167 w/ abst. & trans.	10/05/2001	JAPAN				
	7.	JP-A-2002-012499 w/ abst. & trans.	01/15/2002	JAPAN				
	8.	JP-A-2000-109396 w/ abst. & trans.	04/18/2000	JAPAN				
	9.	JP-A-2002-076007 w/ abst. & trans.	03/15/2002	JAPAN				
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)								
	10.	Talid SINNO et al.; "Modeling Microdefect Formation in Czochralski Silicon"; <i>Journal of the Electrochemical Society</i> ; 146 (6); 1999; pp. 2300-2312.						
EXAMINER							DATE CONSIDERED	
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.								